SUD45N05-20L

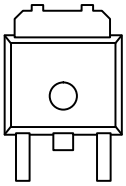
N-Channel Enhancement-Mode Transistor, Logic Level

Product Summary

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)[a]
50	0.018 @ V_{GS} = 10 V	±43
	0.020 @ V_{GS} = 4.5 V	±43

175° C Rated
Maximum Junction Temperature
TrenchFET™
Power MOSFETs

TO-252

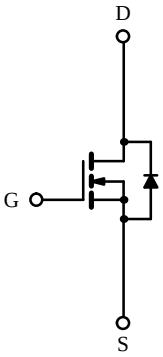


G D S

Top View

Drain Connected to Tab

Order Number:
SUD45N05-20L



N-Channel MOSFET

Absolute Maximum Ratings (T_C = 25°C Unless Otherwise Noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	50	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current[a]	T_C = 25°C	I_D	±43	A
	T_C = 100°C		±30	
Pulsed Drain Current		I_{DM}	±100	
Continuous Source Current (Diode Conduction)[a]		I_S	43	
Avalanche Current		I_{AR}	37	
Repetitive Avalanche Energy (Duty Cycle ≤ 1%)	L = 0.1 mH	E_{AR}	93	mJ
Maximum Power Dissipation	T_C = 25°C	P_D	75	W
	T_A = 25°C		2.5[a]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 175	°C

Thermal Resistance Ratings

Parameter		Symbol	Limit	Unit
Maximum Junction-to-Ambient	Free Air, FR4 Board Mount	R_{thJA}	60	°C/W
	Free Air, Vertical Mount		110	
Maximum Junction-to-Case		R_{thJC}	2.0	

Notes
a. Calculated Rating for T_C = 25°C, for comparison purposes only. This cannot be used as continuous rating (see Absolute Maximum Ratings and Typical Characteristics).
b. Surface Mounted on FR4 Board, t ≤ 10 sec.

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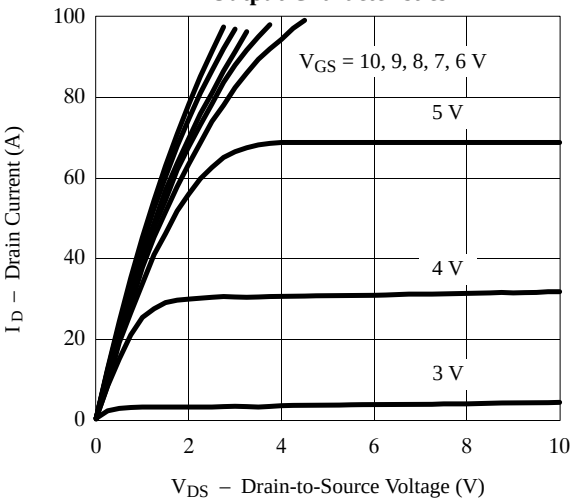
Specifications (T_J = 25°C Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Min	Typ[a]	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 µA	50			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1.0	2.0		
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 50 V, V_{GS} = 0 V			1	µA
		V_{DS} = 50 V, V_{GS} = 0 V, T_J = 125°C			50	
		V_{DS} = 50 V, V_{GS} = 0 V, T_J = 175°C			150	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	43			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A			0.018	Ω
		V_{GS} = 10 V, I_D = 20 A, T_J = 125°C			0.036	
		V_{GS} = 10 V, I_D = 20 A, T_J = 125°C			0.040	
		V_{GS} = 4.5 V, I_D = 43 A			0.020	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 43 A	20			S
Dynamic[a]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		1800	3600	pF
Output Capacitance	C_{oss}			370		
Reverse Transfer Capacitance	C_{rss}			130		
Total Gate Charge[c]	Q_g	V_{DS} = 25 V, V_{GS} = 10 V, I_D = 43 A		43	60	nC
Gate-Source Charge[c]	Q_{gs}			7		
Gate-Drain Charge[c]	Q_{gd}			10		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 25 V, R_L = 0.6 Ω I_D ≅ 43 A, V_{GEN} = 10 V, R_G = 2.5 Ω		10	20	ns
Rise Time[c]	t_r			10	20	
Turn-Off Delay Time[c]	$t_{d(off)}$			32	60	
Fall Time[c]	t_f			7	15	
Source-Drain Diode Ratings and Characteristic (T_C = 25°C)						
Pulsed Current	I_{SM}				43	A
Diode Forward Voltage[b]	V_{SD}	I_F = 43 A, V_{GS} = 0 V			1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 43 A, di/dt = 100 A/µs		49	100	ns

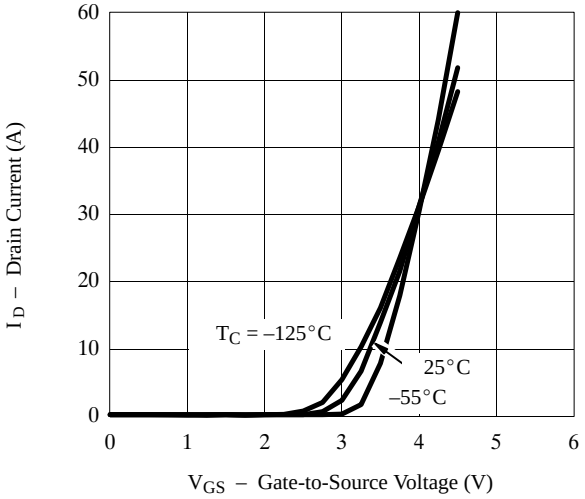
Notes
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
c. Independent of operating temperature.

Typical Characteristics (25°C Unless Otherwise Noted)

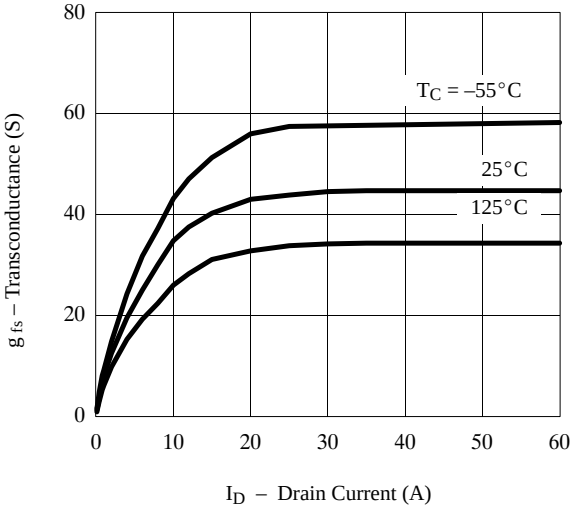
Output Characteristics



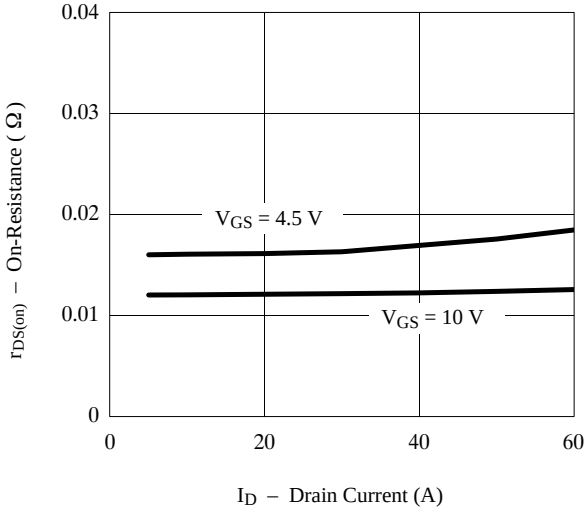
Transfer Characteristics



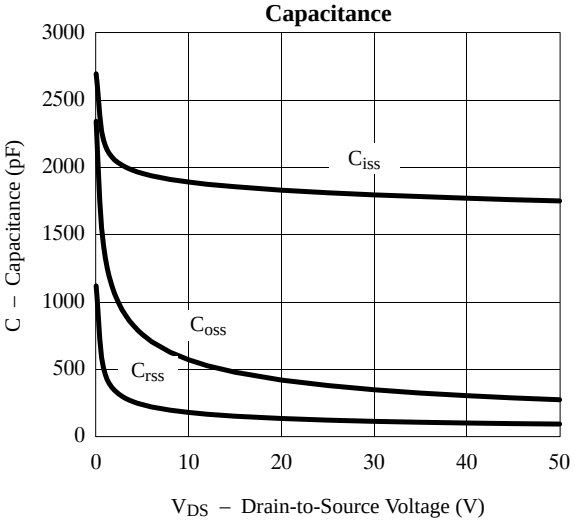
Transconductance



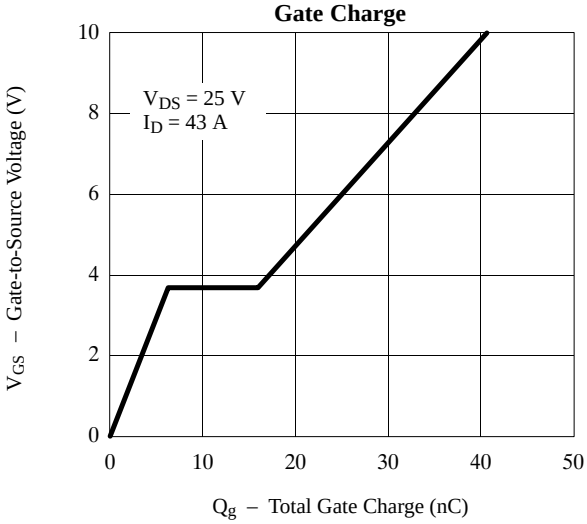
On-Resistance vs. Drain Current



Capacitance

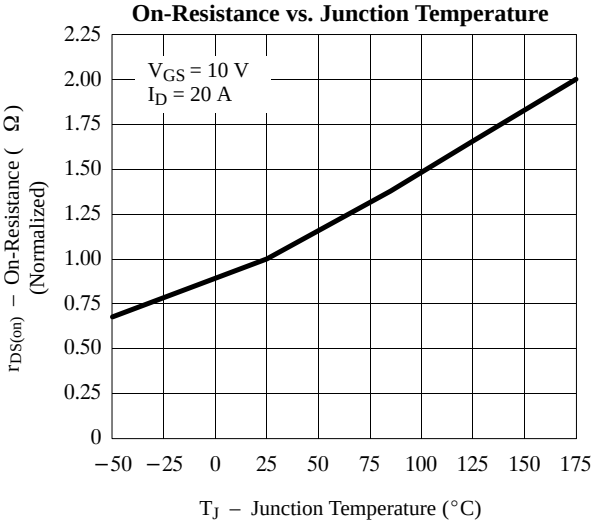


Gate Charge

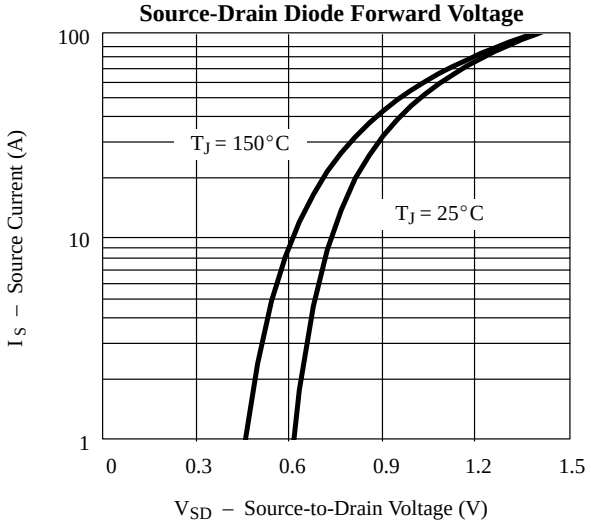


Typical Characteristics (25°C Unless Otherwise Noted)

On-Resistance vs. Junction Temperature

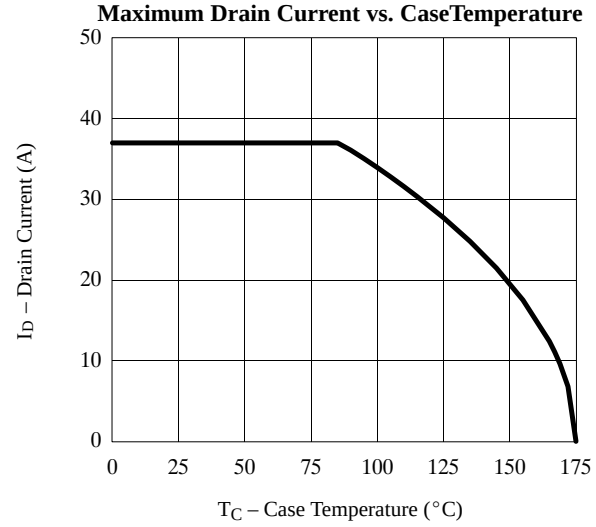


Source-Drain Diode Forward Voltage

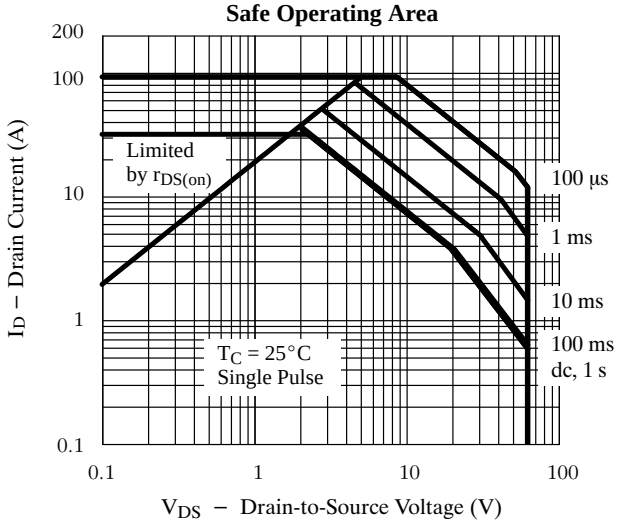


Thermal Ratings

Maximum Drain Current vs. CaseTemperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case